2SC5658M3T5G, 2SC5658RM3T5G

NPN Silicon General Purpose Amplifier Transistor

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Reduces Board Space
- High h_{FE}, 210-460 (typical)
- Low $V_{CE(sat)}$, < 0.5 V
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Available in 8 mm, 7-inch/3000 Unit Tape and Reel
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	50	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	7.0	Vdc
Collector Current – Continuous	I _C	150	mAdc

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	P_{D}	260	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T _{stg}	−55 ~ +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

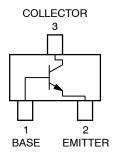
1



ON Semiconductor®

http://onsemi.com

NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT



MARKING DIAGRAM



SOT-723



XX = Specific Device Code (B9 = 2SC5658M3T5G RM = 2SC5658RM3T5G) M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
2SC5658M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel
2SC5658RM3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSV2SC5658M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

2SC5658M3T5G, 2SC5658RM3T5G

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

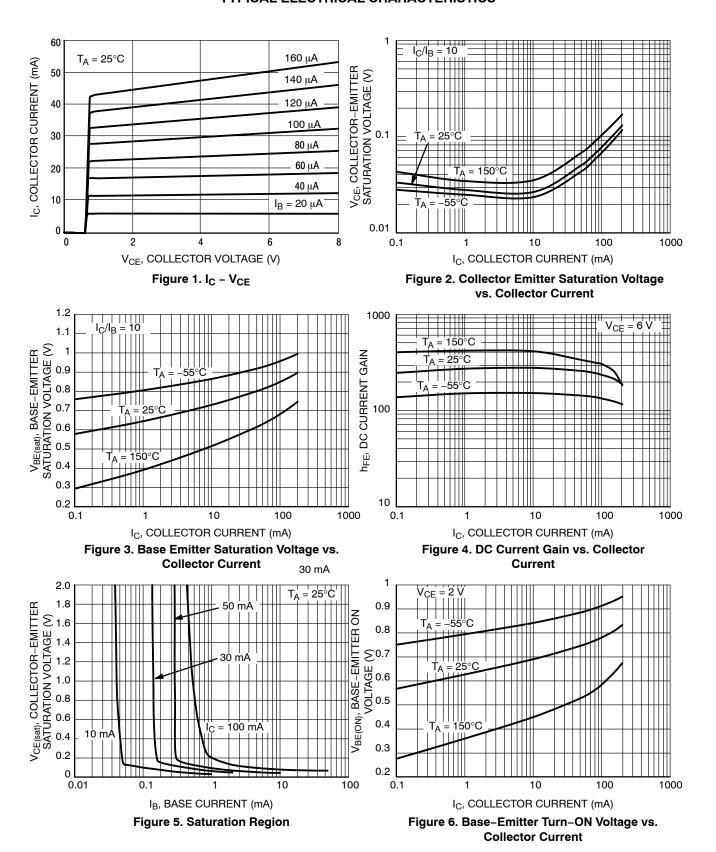
Characteristic	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage (I _C = 50 μAdc, I _E = 0)	V _{(BR)CBO}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (I _C = 1.0 mAdc, I _B = 0)	V _{(BR)CEO}	50	-	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 50 \mu Adc, I_E = 0$)	$V_{(BR)EBO}$	7.0	-	-	Vdc
Collector-Base Cutoff Current (V _{CB} = 30 Vdc, I _E = 0)	I _{CBO}	-	-	0.5	μΑ
Emitter-Base Cutoff Current (V _{EB} = 4.0 Vdc, I _B = 0)	I _{EBO}	-	-	0.5	μΑ
Collector-Emitter Saturation Voltage (Note 2) (I _C = 50 mAdc, I _B = 5.0 mAdc)	V _{CE(sat)}	-	-	0.4	Vdc
	h _{FE}	120 215	- -	560 375	-
Transition Frequency (V _{CE} = 12 Vdc, I _C = 2.0 mAdc, f = 30 MHz)	f _T	=	180	-	MHz
Output Capacitance (V _{CB} = 12 Vdc, I _C = 0 Adc, f = 1.0 MHz)	C _{OB}	_	2.0	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. *Include NSV-prefix devices where applicable.

2. Pulse Test: Pulse Width ≤ 300 µs, D.C. ≤ 2%.

2SC5658M3T5G, 2SC5658RM3T5G

TYPICAL ELECTRICAL CHARACTERISTICS



2SC5658M3T5G, 2SC5658RM3T5G

TYPICAL ELECTRICAL CHARACTERISTICS

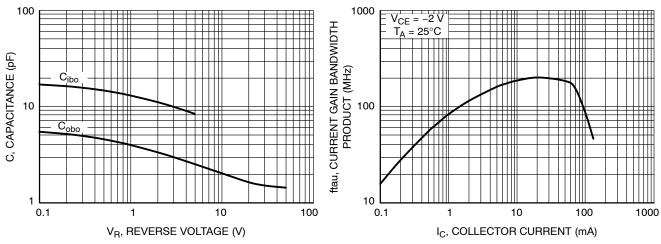


Figure 7. Capacitance

Figure 8. Current Gain Bandwidth Product vs.
Collector Current

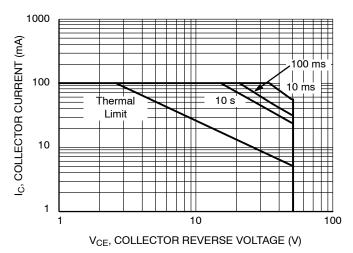


Figure 9. Safe Operating Area



SOT-723 CASE 631AA-01 ISSUE D

DATE 10 AUG 2009

NOTES:

- NOTES.

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD
- FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.45	0.50	0.55	
b	0.15	0.21	0.27	
b1	0.25	0.31	0.37	
С	0.07	0.12	0.17	
D	1.15	1.20	1.25	
E	0.75	0.80	0.85	
е	0.40 BSC			
ΗE	1.15	1.20	1.25	
L	0.29 REF			
12	0.15	0.20	0.25	

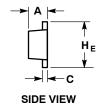
L2 0.15 0.20 0.25 **GENERIC** MARKING DIAGRAM*

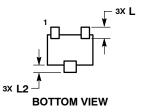


= Specific Device Code XX Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G", may or not be present.

-X-2X b ⊕ 0.08 X Y **TOP VIEW**

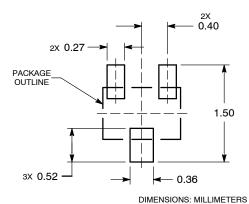




STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-723		PAGE 1 OF 1

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative